

Data sheet acquired from Harris Semiconductor SCHS187C

January 1998 - Revised July 2003

Features

- Common Latch-Enable Control
- Common Three-State Output Enable Control
- Buffered Inputs
- Three-State Outputs
- Bus Line Driving Capacity
- Typical Propagation Delay = 13ns at V_{CC} = 5V, $C_L = 15 pF$, $T_A = 25^{\circ}C$ (Data to Output)
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range ... -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: NIL = 30%, NIH = 30% of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V (Max), V_{IH} = 2V (Min)$
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OI} , V_{OH}

CD54/74HC533, CD54/74HCT533, CD54/74HC563, CD74HCT563

High-Speed CMOS Logic Octal Inverting Transparent Latch, Three-State Outputs

Description

The 'HC533, 'HCT533, 'HC563, and CD74HCT563 are high-speed Octal Transparent Latches manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL devices.

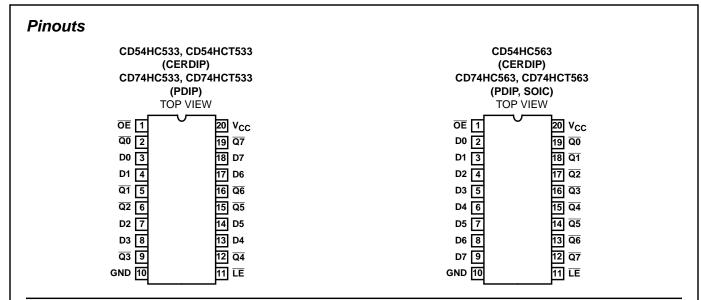
The outputs are transparent to the inputs when the latch enable (\overline{LE}) is high. When the latch enable (\overline{LE}) goes low the data is latched. The output enable (\overline{OE}) controls the three-state outputs. When the output enable (\overline{OE}) is high the outputs are in the high impedance state. The latch operation is independent of the state of the output enable.

The 'HC533 and 'HCT533 are identical in function to the 'HC563 and CD74HCT563 but have different pinouts. The 'HC533 and 'HCT533 are similar to the 'HC373 and 'HCT373; the latter are non-inverting types.

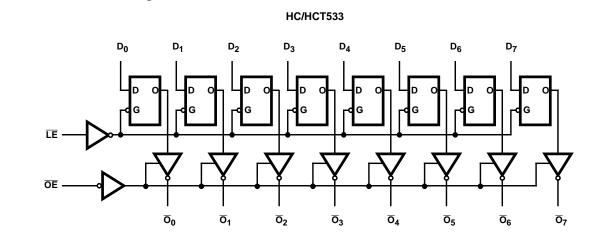
Ordering Information

PART NUMBER	TEMP. RANGE (^o C)	PACKAGE
CD54HC533F3A	-55 to 125	20 Ld CERDIP
CD54HC563F3A	-55 to 125	20 Ld CERDIP
CD54HCT533F3A	-55 to 125	20 Ld CERDIP
CD74HC533E	-55 to 125	20 Ld PDIP
CD74HC563E	-55 to 125	20 Ld PDIP
CD74HC563M	-55 to 125	20 Ld SOIC
CD74HCT533E	-55 to 125	20 Ld PDIP
CD74HCT563E	-55 to 125	20 Ld PDIP
CD74HCT563M	-55 to 125	20 Ld SOIC

CAUTION: These devices are sensitive to electrostatic discharge. Users should follow proper IC Handling Procedures. Copyright © 2003, Texas Instruments Incorporated



Functional Block Diagram



TRUTH TABLE

OUTPUT ENABLE	LATCH ENABLE	DATA	Q OUTPUT
L	Н	Н	L
L	Н	L	н
L	L	I	Н
L	L	h	L
Н	Х	Х	Z

H = High Voltage Level, L = Low Voltage Level, X = Don't Care, Z = High Impedance State, I = Low voltage level one set-up time prior to the high to low latch enable transition, h = High voltage level one set-up time prior to the high to low latch enable transition.

Absolute Maximum Ratings

DC Supply Voltage, V _{CC} 0.5V to 7V DC Input Diode Current, I _{IK}
For $V_{l} < -0.5V$ or $V_{l} > V_{CC} + 0.5V$
DC Output Diode Current, IOK
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$
DC Drain Current, per Output, I _O
For -0.5V < V _O < V _{CC} + 0.5V±35mA
DC Output Source or Sink Current per Output Pin, IO
For $V_0 > -0.5V$ or $V_0 < V_{CC} + 0.5V$ ±25mA
DC V _{CC} or Ground Current, I _{CC} ±50mA

Operating Conditions

Temperature Range, T_A
Supply Voltage Range, V _{CC}
HC Types
HCT Types
DC Input or Output Voltage, VI, VO 0V to VCC
Input Rise and Fall Time
2V
4.5V 500ns (Max)
6V

Thermal Information

Thermal Resistance (Typical, Note 1)	θ _{JA} (^o C/W)
E (PDIP) Package	. 69
M (SOIC) Package	. 58
Maximum Junction Temperature	150 ⁰ C
Maximum Storage Temperature Range	65 ^o C to 150 ^o C
Maximum Lead Temperature (Soldering 10s)	300 ⁰ C
(SOIC - Lead Tips Only)	

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

1. The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

		TEST CONDITIONS			25 ⁰ C			-40°C TO 85°C		-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES			_						_			-
High Level Input Voltage	V _{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input	V _{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
Voltage				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output	V _{OH}	V _{IH} or	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
Voltage CMOS Loads		VIL	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
0			-0.02	6	5.9	-	-	5.9	-	5.9	-	V
High Level Output			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Voltage TTL Loads			-7.8	6	5.48	-	-	5.34	-	5.2	-	V
Low Level Output	V _{OL}	V _{IH} or	0.02	2	-	-	0.1	-	0.1	-	0.1	V
Voltage CMOS Loads		V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Voltage TTL Loads			7.8	6	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lı	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	Icc	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μA

CD54/74HC533, CD54/74HCT533, CD54/74HC563, CD74HCT563

		TEST CONDITIONS			25 ⁰ C			-40 ⁰ C TO 85 ⁰ C		-55°C TO 125°C		
PARAMETER	SYMBOL	V _I (V)	I _O (mA)	V _{CC} (V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
Three-State Leakage Current	-	V _{IL} or V _{IH}	V _O = V _{CC} or GND	6	-	-	±0.5	-	±5	-	±10	μA
HCT TYPES												
High Level Input Voltage	VIH	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	lı	V _{CC} to GND	-	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	Icc	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Three-State Leakage Current	-	V _{IL} or V _{IH}	V _O = V _{CC} or GND	5.5	-	-	±0.5	-	±5	-	±10	μΑ
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 2)	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μΑ

NOTE:

2. For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
D0 - D7	0.15
LE	0.30
ŌĒ	0.55

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360µA max at 25°C.

CD54/74HC533, CD54/74HCT533, CD54/74HC563, CD74HCT563

Prerequisite For Switching Specifications

		TEST	v _{cc}		25 ⁰ C		-40 ⁰ C T	O 85 ⁰ C	-55°C T	O 125 ⁰ C	
PARAMETER	SYMBOL	CONDITIONS	(V)	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNITS
HC TYPES											
LE Pulse Width	t _W	-	2	80	-	-	100	-	120	-	ns
			4.5	16	-	-	20	-	24	-	ns
			6	14	-	-	17	-	20	-	ns
Set-up Time Data to LE	ts∪	-	2	50	-	-	65	-	75	-	ns
			4.5	10	-	-	13	-	15	-	ns
			6	9	-	-	11	-	13	-	ns
Hold Time, Data to $\overline{\text{LE}}$	t _H	-	2	35	-	-	45	-	55	-	ns
(533)			4.5	7	-	-	9	-	11	-	ns
			6	6	-	-	8	-	7	-	ns
Hold Time, Data to $\overline{\text{LE}}$	t _H	-	2	4	-	-	4	-	4	-	ns
(563)			4.5	4	-	-	4	-	4	-	ns
			6	4	-	-	4	-	4	-	ns
HCT TYPES	•	•									
LE Pulse Width	t _w	-	4.5	16	-	-	20	-	24	-	ns
Set-up Time Data to LE	tw	-	4.5	10	-	-	13	-	15	-	ns
Hold Time, Data to $\overline{\text{LE}}$ (533)	t _H	-	4.5	8	-	-	10	-	12	-	ns
Hold Time, Data to LE (563)	t _H	-	4.5	5	-	-	5	-	5	-	ns

Switching Specifications Input t_r, t_f = 6ns

		TEST		25 ⁰ C		-40 ⁰ C TO 85 ⁰ C	-55 ⁰ C TO 125 ⁰ C	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	TYP	MAX	МАХ	MAX	
HC TYPES								
Propagation Delay,	t _{PLH} , t _{PHL}	C _L = 50pF	2	-	165	205	250	ns
Data to Qn (HC533)			4.5	-	33	41	50	ns
X ,			6	-	28	35	43	ns
		C _L = 15pF	5	13	-	-	-	ns
Propagation Delay, Data to Qn (HC563)	^t PLH, ^t PHL	C _L = 50pF	2	-	150	190	225	ns
			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C _L = 15pF	5	12	-	-	-	ns
Propagation Delay,	^t PLH, ^t PHL	C _L = 50pF	2	-	175	220	265	ns
LE to Qn (HC533)			4.5	-	35	44	53	ns
()			6	-	30	37	45	ns
		C _L = 15pF	5	14	-	-	-	ns
Propagation Delay,	^t PLH, ^t PHL	C _L = 50pF	2	-	165	205	250	ns
LE to Qn (HC563)			4.5	-	33	41	50	ns
(6	-	28	35	43	ns
		C _L = 15pF	5	13	-	- 1	-	ns

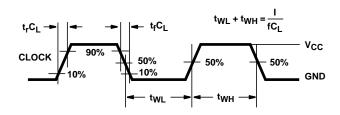
		TEST		25	5°C	-40 ⁰ C TO 85 ⁰ C	-55°C TO 125 [°] C	
PARAMETER	SYMBOL	CONDITIONS	V _{CC} (V)	TYP	MAX	МАХ	MAX	
Enable Times	t _{PZH} , t _{PZL}	C _L = 50pF	2	-	150	190	225	ns
(HC533)			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C _L = 15pF	5	12	-	-	-	ns
Disable Times	tPHZ, tPLZ	C _L = 50pF	2	-	150	190	225	ns
(HC533)			4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C _L = 15pF	5	12	-	-	-	ns
Enable and Disable Times	^t PZH, ^t PZL,	C _L = 50pF	2	-	150	190	225	ns
(HC563)	^t PHZ, ^t PLZ		4.5	-	30	38	45	ns
			6	-	26	33	38	ns
		C _L = 15pF	5	12	-	-	-	ns
Input Capacitance	Cl	-	-	-	10	10	10	pF
Three-State Output Capacitance	C _O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	-	5	42	-	-	-	pF
HCT TYPES								
Propagation Delay, Data to Qn	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	34	43	51	ns
(HC/HCT533)		C _L = 15pF	5	14	-	-	-	ns
Propagation Delay,	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	30	38	45	ns
Data to Qn (HC/HCT563)		C _L = 15pF	5	12	-	-	-	ns
Propagation Delay,	t _{PLH} , t _{PHL}	C _L = 50pF	4.5	-	38	48	57	ns
LE to Qn (HC/HCT533)		C _L = 15pF	5	16	-	-	-	ns
Propagation Delay,	t _{PZL} , t _{PZH}	C _L = 50pF	4.5	-	35	44	53	ns
LE to Qn (HC/HCT563)		C _L = 15pF	5	14	-	-	-	ns
Enable Times	t _{PLZ} , t _{PZH}	C _L = 50pF	4.5	-	35	44	53	ns
(HC/HCT533)		C _L = 15pF	5	14	-	- 1	-	ns
Disable Times	t _{TLH} , t _{THL}	C _L = 50pF	4.5	-	30	38	45	ns
(HC/HCT533)		C _L = 15pF	5	12	-	-	-	ns
Enable and Disable Times	t _{PZH} , t _{PZL} ,	C _L = 50pF	4.5	-	35	44	53	ns
(HC/HCT563)	^t PHZ, ^t PLZ	C _L = 15pF	5	14	-	-	-	ns
Input Capacitance	Cl	-	-	-	10	10	10	pF
Power Dissipation Capacitance (Notes 3, 4)	C _{PD}	-	5	42	-	-	-	pF

NOTES:

3. C_{PD} is used to determine the no-load dynamic power consumption, per latch.

4. P_D (total power per latch) = C_{PD} V_{CC}² f_i + Σ C_L V_{CC}² f_o where f_i = Input Frequency, f_o = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms



NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX} , input duty cycle = 50%.

FIGURE 1. HC CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH

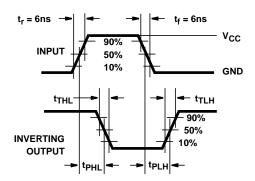
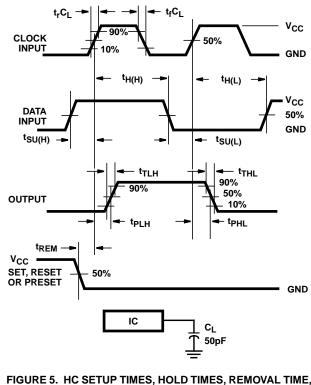
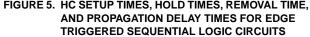
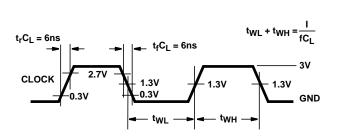


FIGURE 3. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

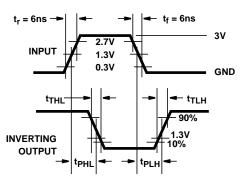


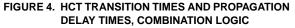


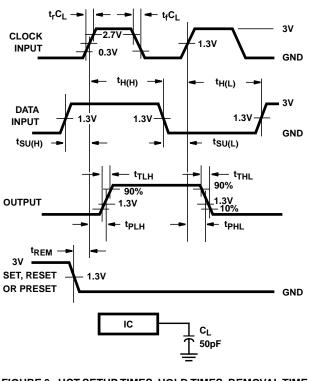


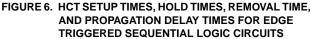
NOTE: Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{MAX} , input duty cycle = 50%.

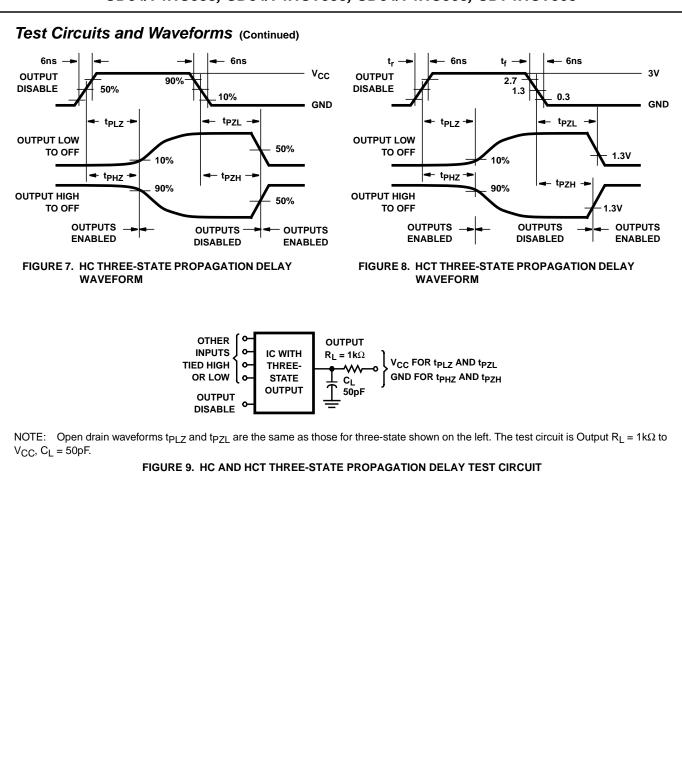
FIGURE 2. HCT CLOCK PULSE RISE AND FALL TIMES AND PULSE WIDTH













PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8606201RA	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8606201RA CD54HC563F3A	Samples
5962-8681301RA	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8681301RA CD54HC533F3A	Samples
CD54HC533F3A	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8681301RA CD54HC533F3A	Samples
CD54HC563F3A	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8606201RA CD54HC563F3A	Samples
CD54HCT533F3A	ACTIVE	CDIP	J	20	20	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	CD54HCT533F3A	Samples
CD74HC533E	ACTIVE	PDIP	Ν	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC533E	Samples
CD74HC563E	ACTIVE	PDIP	Ν	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HC563E	Samples
CD74HCT533E	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT533E	Samples
CD74HCT563E	ACTIVE	PDIP	N	20	20	RoHS & Green	NIPDAU	N / A for Pkg Type	-55 to 125	CD74HCT563E	Samples
CD74HCT563M	ACTIVE	SOIC	DW	20	25	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HCT563M	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



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PACKAGE OPTION ADDENDUM

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF CD54HC533, CD54HC563, CD54HCT533, CD74HC533, CD74HC563, CD74HCT533 :

- Catalog : CD74HC533, CD74HC563, CD74HCT533
- Military : CD54HC533, CD54HC563, CD54HCT533

NOTE: Qualified Version Definitions:

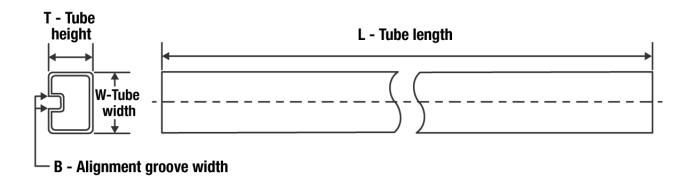
- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications



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TUBE



*All o	dimensions	are	nominal
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Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
CD74HC533E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HC563E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HCT533E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HCT563E	N	PDIP	20	20	506	13.97	11230	4.32
CD74HCT563M	DW	SOIC	20	25	507	12.83	5080	6.6

J (R-GDIP-T**) 14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package is hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
- E. Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- \triangle The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW0020A



PACKAGE OUTLINE

SOIC - 2.65 mm max height

SOIC



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice. 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm per side.
- 5. Reference JEDEC registration MS-013.



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EXAMPLE BOARD LAYOUT

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



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EXAMPLE STENCIL DESIGN

SOIC - 2.65 mm max height

SOIC



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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